

General Description

The 40N03B is N-channel MOSFET device that features a low on-state resistance and excellent switching characteristics, and designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

Features

- Simple Drive Requirement
- Low On-Resistance
- 100% avalanche tested
- RoHS Compliant

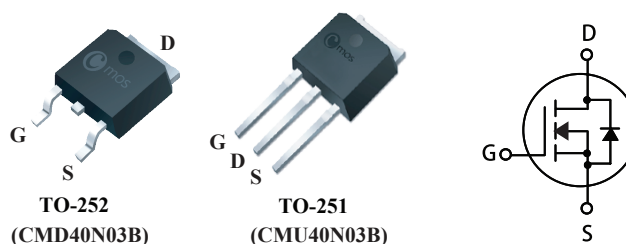
Product Summary

BVDSS	R _{DS(on)} max.	ID
30V	20mΩ	36A

Applications

- CPU Power Delivery
- DC/DC converter
- Switching applications

TO-252/251 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _C =25°C	Continuous Drain Current ¹	36	A
I _D @T _C =100°C	Continuous Drain Current	25	A
I _{DM}	Pulsed Drain Current ²	144	A
EAS	Single Pulse Avalanche Energy ³	36	mJ
P _D @T _C =25°C	Total Power Dissipation	45	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient	---	45	°C/W
R _{θJC}	Thermal Resistance Junction-case	---	2.78	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=10A$	---	17.5	20	mΩ
		$V_{GS}=4.8V$, $I_D=8A$	---	25	42	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	uA
		$V_{DS}=24V$, $V_{GS}=0V$, $T_J=125^{\circ}\text{C}$	---	---	10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=10A$	---	10	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.1	---	Ω
Q_g	Total Gate Charge	$V_{DS}=15V$, $V_{GS}=4.5V$, $I_D=20A$	---	9	---	nC
Q_{gs}	Gate-Source Charge		---	4.5	---	
Q_{gd}	Gate-Drain Charge		---	2.6	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$, $V_{GS}=10V$, $R_G=3.3\Omega$ $I_D=20A$	---	8	---	ns
T_r	Rise Time		---	75	---	
$T_{d(off)}$	Turn-Off Delay Time		---	30	---	
T_f	Fall Time		---	25	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	600	---	pF
C_{oss}	Output Capacitance		---	80	---	
C_{rss}	Reverse Transfer Capacitance		---	70	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ¹	$V_G=V_D=0V$, Force Current	---	---	36	A
I_{SM}	Pulsed Source Current ²		---	---	144	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=8A$, $T_J=25^{\circ}\text{C}$	---	---	1.2	V

Note :

1.Limited by wire bonding

2.Pulse width limited by safe operating area

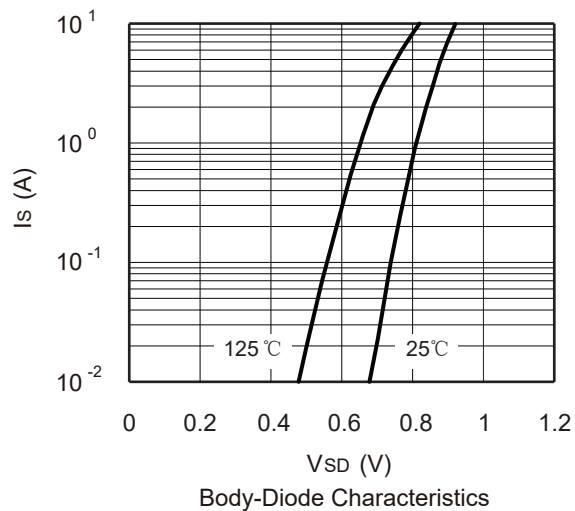
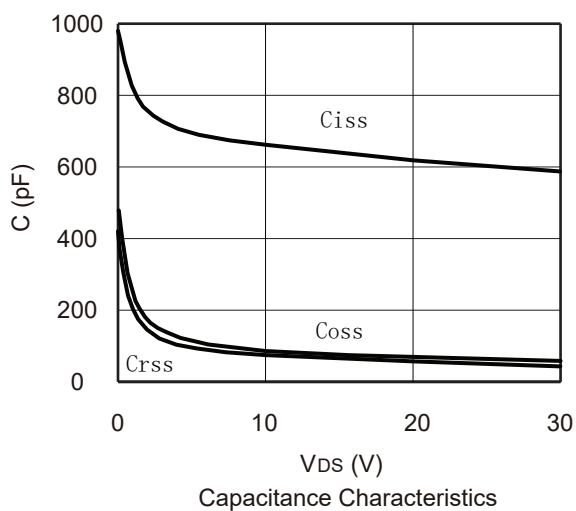
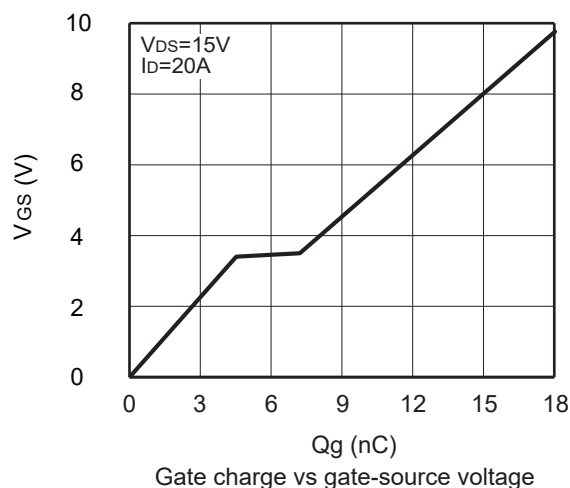
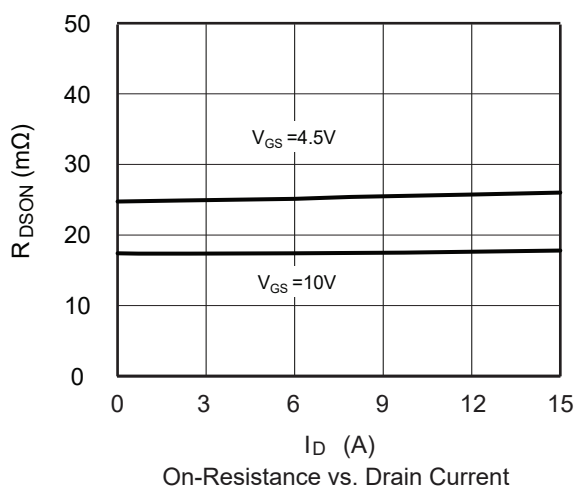
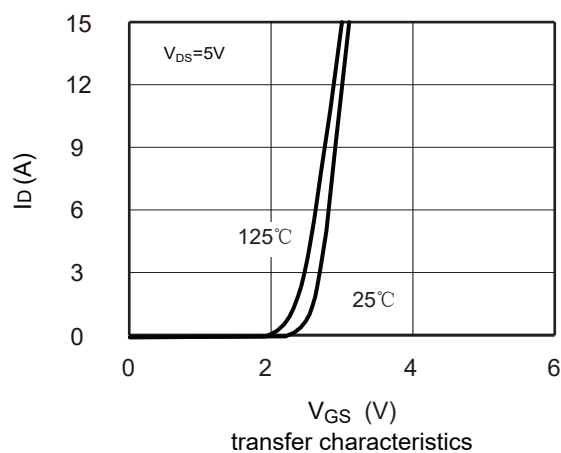
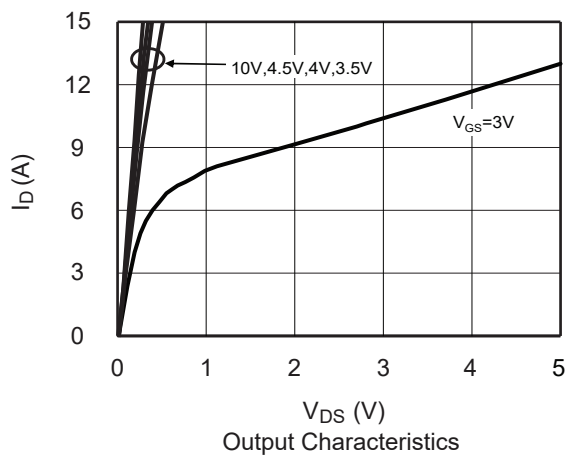
3.The EAS data shows Max. rating . The test condition is $V_{DD}=20V$, $V_{GS}=10V$, $L=0.5\text{mH}$, $I_{AS}=12A$

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Cmos reserves the right to improve product design ,functions and reliability without notice.Please refer to the latest version of specification.

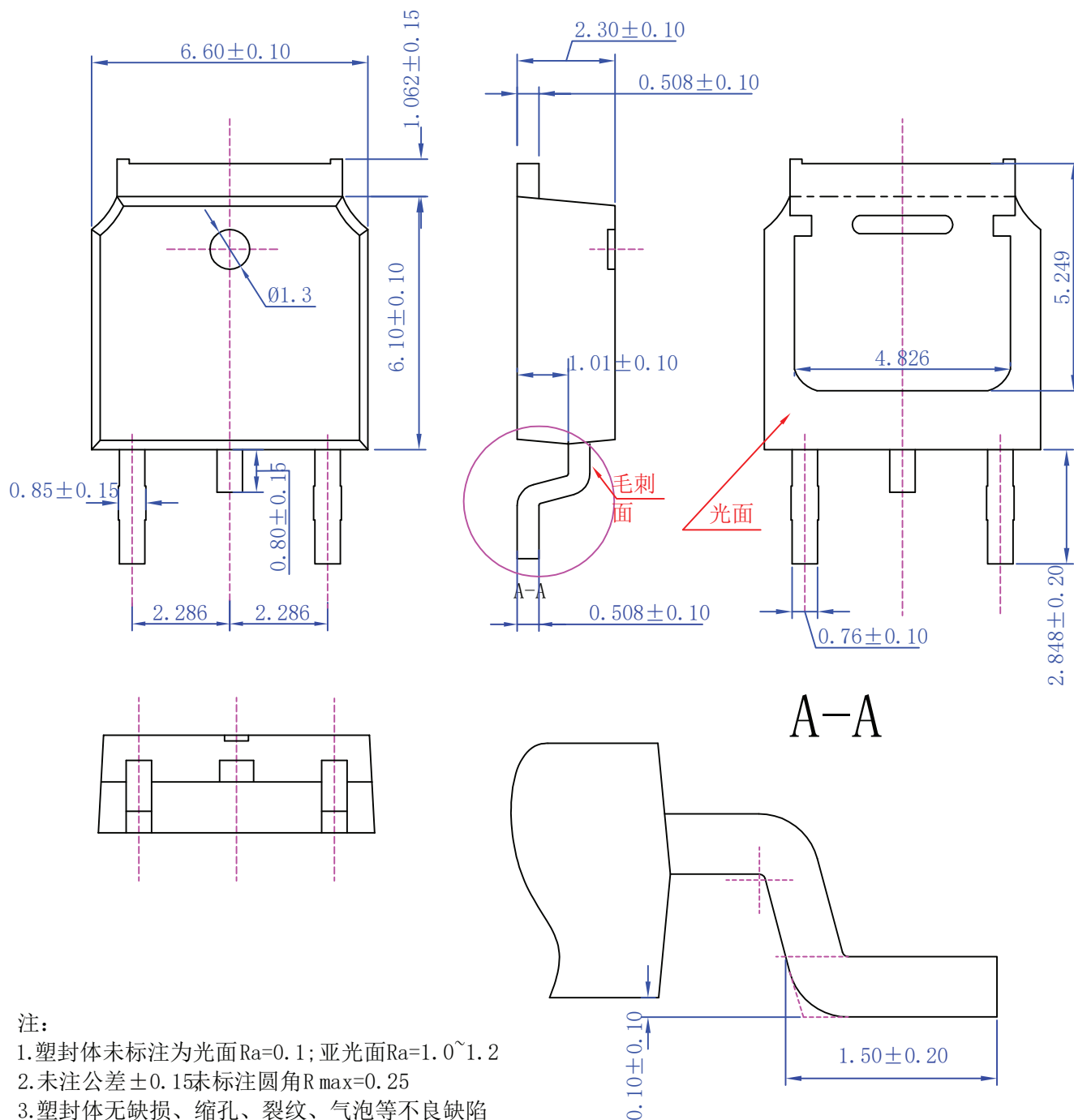
Typical Characteristics



Package Dimension

TO-252

Unit :mm



注:

1. 塑封体未标注为光面 $R_a=0.1$; 亚光面 $R_a=1.0 \sim 1.2$
2. 未注公差 ± 0.15 未标注圆角 $R_{max}=0.25$
3. 塑封体无缺损、缩孔、裂纹、气泡等不良缺陷
4. 标注单位mm
5. 顶针孔不允许凸出塑封体表面

Package Dimension

TO-251A

Unit :mm

